

Data Sheet Issue:- 2

# Rectifier Diode Types W2134NC300 to W2134NC400 Previous Type No.: SW26-36CXC635

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V <sub>RRM</sub>	Repetitive peak reverse voltage, (note 1)	3000-4000	V
Vrsm	Non-repetitive peak reverse voltage, (note 1)	3100-4100	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
IF(AV)M	Maximum average forward current, T <sub>sink</sub> =55°C, (note 2)	2134	А
IF(AV)M	Maximum average forward current. T <sub>sink</sub> =100°C, (note 2)	1494	А
IF(RMS)M	Nominal RMS forward current, T <sub>sink</sub> =25°C, (note 2)	3910	А
I <sub>F(d.c.)</sub>	D.C. forward current, T <sub>sink</sub> =25°C, (note 3)	3472	А
IFSM	Peak non-repetitive surge t <sub>p</sub> =10ms, V <sub>rm</sub> =60%V <sub>RRM</sub> , (note 4)	20.0	kA
IFSM2	Peak non-repetitive surge t <sub>P</sub> =10ms, Vrm≤10V, (note 4)	24.0	kA
l²t	I <sup>2</sup> t capacity for fusing $t_p$ =10ms, $V_{rm}$ =60% $V_{RRM}$ , (note 4)	2.0×10 <sup>6</sup>	A <sup>2</sup> s
l²t	I <sup>2</sup> t capacity for fusing $t_p=10$ ms, $V_{rm} \le 10$ V, (note 4)	2.88×10 <sup>6</sup>	A <sup>2</sup> s
T <sub>j op</sub>	Operating temperature range	-55 to +160	°C
T <sub>stg</sub>	Storage temperature range	-55 to +190	°C

Notes:-

1) De-rating factor of 0.13% per °C is applicable for  $T_j$  below 25°C.

2) Double side cooled, single phase; 50Hz, 180° half-sinewave.

3) Double side cooled.

4) Half-sinewave, 160°C T<sub>j</sub> initial.



# **Characteristics**

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
Vfm	Maximum peak forward voltage	-	-	1.86	IFM=3800A	V
V <sub>T0</sub>	Threshold voltage	-	-	0.865		V
r⊤	Slope resistance	-	-	0.26		mΩ
I <sub>RRM</sub>	Peak reverse current	-	-	50	Rated V <sub>RRM</sub>	mA
	Thermal registeres, junction to besteink	-	-	0.022	Double side cooled	K/W
RthJK	Thermal resistance, junction to heatsink	-	-	0.044	Single side cooled	K/W
F	Mounting force	19	-	26	Note 2	kN
Wt	Weight		480			g

Notes:-

1) Unless otherwise indicated  $T_j=160^{\circ}C$ .

2) For other clamp forces, please consult factory.



## **Notes on Ratings and Characteristics**

## 1.0 Voltage Grade Table

Voltage Grade	V <sub>RRM</sub> V	V <sub>RSM</sub> V	V <sub>R</sub> DC V
30	3000	3100	1750
40	4000	4100	2000

#### 2.0 Extension of Voltage Grades

This report is applicable to other voltage grades when supply has been agreed by Sales/Production.

#### 3.0 De-rating Factor

A blocking voltage de-rating factor of 0.13%/°C is applicable to this device for T<sub>j</sub> below 25°C.

### 4.0 Snubber Components

When selecting snubber components, care must be taken not to use excessively large values of snubber capacitor or excessively small values of snubber resistor. Such excessive component values may lead to device damage due to the large resultant values of snubber discharge current. If required, please consult the factory for assistance.

#### 5.0 Computer Modelling Parameters

### 5.1 Device Dissipation Calculations

Where  $V_{T0}=0.865V$ ,  $r_T=0.26m\Omega$ ,

 $R_{th}$  = Supplementary thermal impedance, see table below and

ff = Form factor, see table below.

Supplementary Thermal Impedance							
Conduction Angle	6 phase (60°)	3 phase (120°)	½ wave (180°)	d.c.			
Square wave Double Side Cooled	0.0320	0.0274	0.0253	0.022			
Square wave Cathode Side Cooled	0.0540	0.0497	0.0477	0.044			
Sine wave Double Side Cooled	0.0271	0.0229	0.022				
Sine wave Cathode Side Cooled	0.0496	0.0467	0.044				

Form Factors						
Conduction Angle6 phase (60°)3 phase (120°)½ wave (180°)						
Square wave	2.449	1.732	1.414	1		
Sine wave	2.778	1.879	1.57			



#### 5.2 Calculating VF using ABCD Coefficients

The on-state characteristic IF vs. VF, on page 8 is represented in two ways;

- (i) the well established  $V_{T0}$  and  $r_T$  tangent used for rating purposes and
- (ii) a set of constants A, B, C, D, forming the coefficients of the representative equation for V<sub>F</sub> in terms of I<sub>F</sub> given below:

$$V_F = A + B \cdot \ln(I_F) + C \cdot I_F + D \cdot \sqrt{I_F}$$

The constants, derived by curve fitting software, are given below for both hot and cold characteristics. The resulting values for  $V_F$  agree with the true device characteristic over a current range, which is limited to that plotted.

25°C Coefficients		160°C Coefficients		
А	1.075751	А	0.7000012	
В	-0.01870484	В	0.04239071	
С	0.1119432×10 <sup>-3</sup>	С	0.2948272×10 <sup>-3</sup>	
D	4.173847×10 <sup>-3</sup>	D	-5.121299×10 <sup>-3</sup>	



5.3 D.C. Thermal Impedance Calculation

$$r_t = \sum_{p=1}^{p=n} r_p \cdot \left(1 - e^{\frac{-t}{\tau_p}}\right)$$

Where p = 1 to *n*, *n* is the number of terms in the series and:

- t = Duration of heating pulse in seconds.
- $r_t =$  Thermal resistance at time t.
- $r_p$  = Amplitude of  $p_{th}$  term.
- $\tau_p$  = Time Constant of r<sub>th</sub> term.

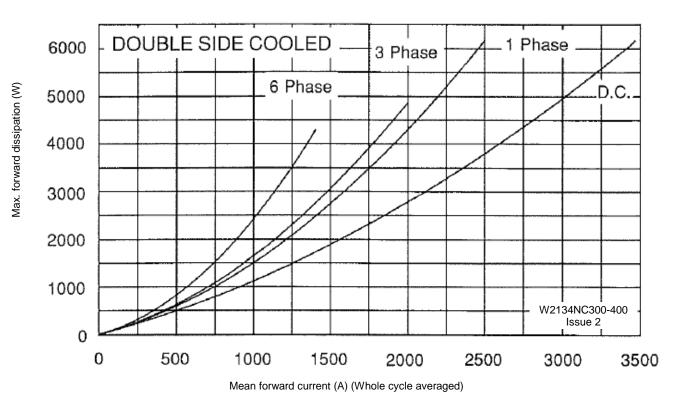
The coefficients for this device are shown in the tables below:

D.C. Double Side Cooled							
Term	rm 1 2 3 4 5						
r <sub>p</sub>	0.01155655	5.055660×10 <sup>-3</sup>	2.503056×10 <sup>-3</sup>	1.549315×10 <sup>-3</sup>	1.736643×10 <sup>-3</sup>		
τρ	0.9222825	0.1703512	0.0453273	0.01143316	0.01582146		

D.C. Single Side Cooled								
Term	Term 1 2 3 4 5 6							
r <sub>p</sub>	0.0280202	4.27556×10 <sup>-3</sup>	5.20318×10 <sup>-3</sup>	3.71583×10 <sup>-3</sup>	2.00592×10 <sup>-3</sup>	1.70787×10 <sup>-3</sup>		
τρ	5.445791	2.121661	0.248842	0.0761462	0.0140677	0.0171541		



# <u>Curves</u>



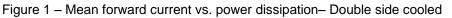
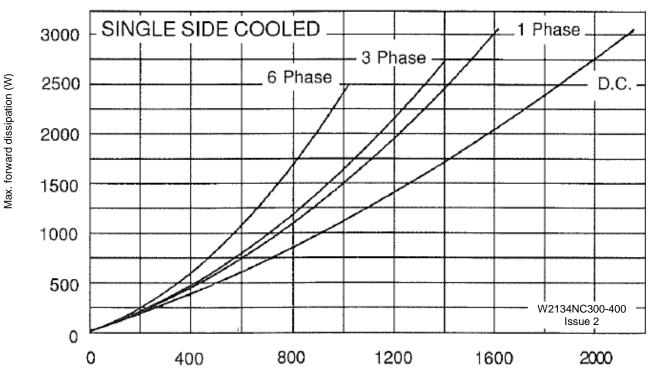
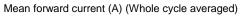


Figure 2 – Mean forward current vs. power dissipation – Single side cooled







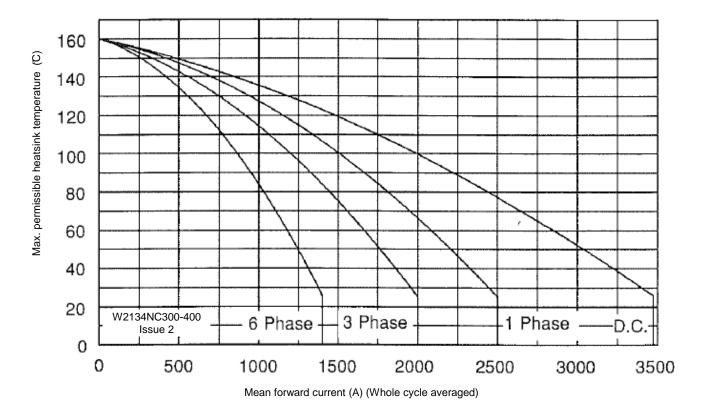
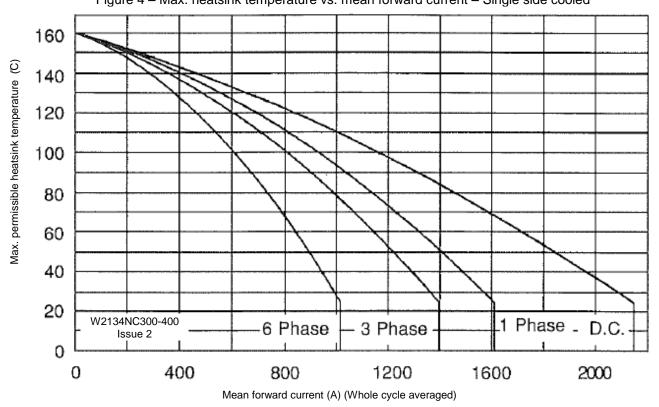


Figure 3 – Max. heatsink temperature vs. mean forward current – Double side cooled

Figure 4 – Max. heatsink temperature vs. mean forward current – Single side cooled





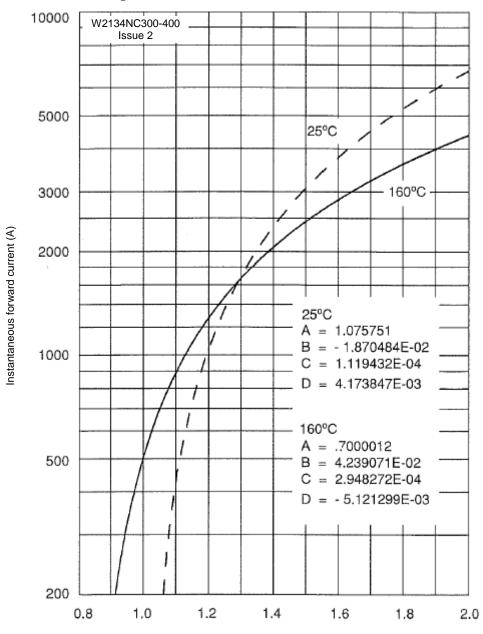


Figure 5 - Forward characteristics of limit device

Instantaneous forward voltage (V)



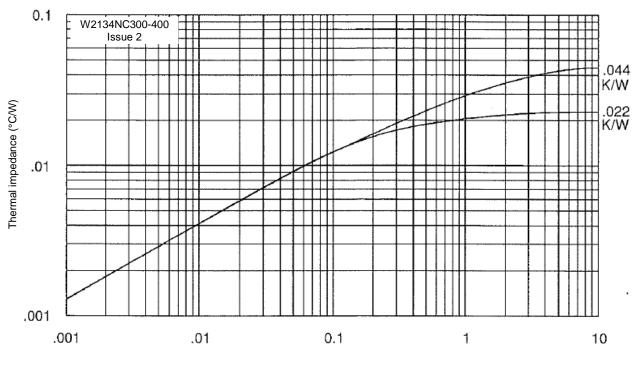
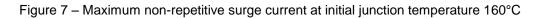
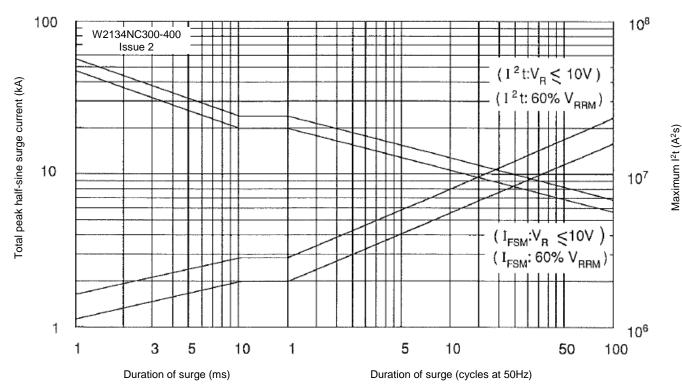


Figure 6 – Transient thermal impedance

Time (s)







# **Outline Drawing & Ordering Information**

